



3DD155(3DD156)

NPN Silicon Low Frequency High Power Transistor



Features:

1. Using triple-diffusion process.Excellent capacity in anti-burnout.Excellent second breakdown capacity.
2. Good temperature stability.Excellent thermal fatigue capability.
3. Implementation of standards: GJB33 A-97, QZJ840611A, QZJ840611
4. Use for Low-speed switch,low frequency power amplify,power adjustment.
5. Quality Class: JP, JT, JCT, GS, G, G+

TECHNICAL DATA:

(Ta = 25°C)

Parameter name	Symbols	Unit	Specifications						Test Condition
			A	B	C	D	E	F	
Collector-Emitter Voltage	V _{CEO}	V	50	100	150	200	250	300	
Emitter-Base Voltage	V _{EBO}	V	5						
Max. Collector Current	I _{CM}	A	2.0						
Max. Collector Dissipation	P _{CM}	W	20						Tc:75°C
Junction Temperature	T _{jm}	°C	175						
Storage Temperature	T _{stg}	°C	-55~+175						
Collector-Emitter Leakage Current	I _{CEO}	mA	Max.:0.5						A:V _{CE} =30V;B:V _{CE} =50V; C~F:V _{CE} =100V
Collector- Emitter Saturation Voltage Drop	V _{CE(sat)}	V	Max.:1.0						I _C =1.0A,I _B =0.1A
DC Current Gain	h _{FE}		Min.:15,Max.:180						V _{CE} =5V,I _C =1.0A
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	V	A	B	C	D	E	F	I _C =1mA
			50	100	150	200	250	300	
C-Base Breakdown Voltage	V _{(BR)CBO}	V	80	150	200	250	350	400	I _C =1mA
E-Base Breakdown Voltage	V _{(BR)EBO}	V	5						I _E =0.5mA

h_{FE} Colored:

Color	Red	Orange	Yellow	Green	Blue	Purple
h _{FE}	15~25	25~40	40~55	55~80	80~120	120~180

Outline and Dimensions: